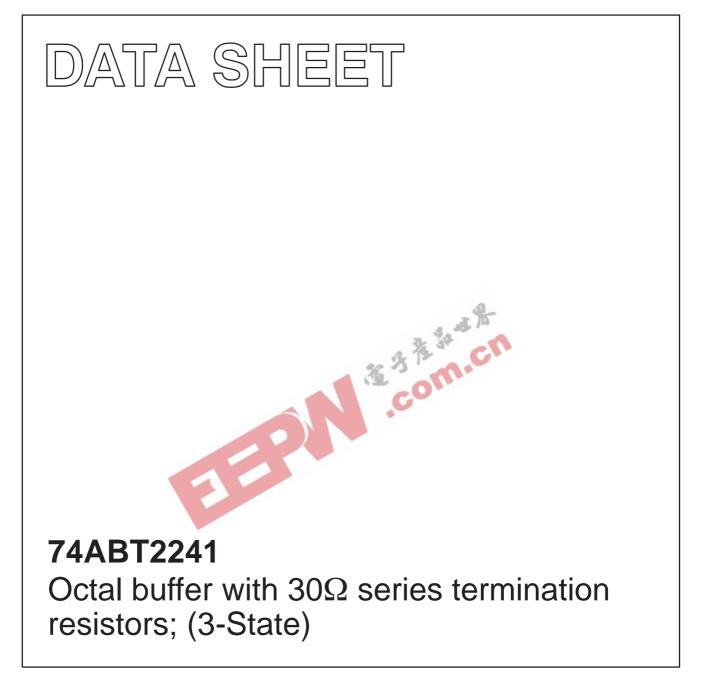
# INTEGRATED CIRCUITS



Product specification IC23 Data Handbook 1996 Sep 30

**PHILIPS** 

74ABT2241

### **FEATURES**

- Octal bus interface
- 3-State buffers
- Power-up 3-State
- Output capability: +12mA/-32mA
- Latch-up protection exceeds 500mA per Jedec Std 17
- ESD protection exceeds 2000 V per MIL STD 883 Method 3015 and 200 V per Machine Model

### DESCRIPTION

The 74ABT2241 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT2241 device is an octal buffer that is ideal for driving bus lines. The device features two Output Enables (10E, 20E), each controlling four of the 3-State outputs.

The 74ABT2241 is designed with  $30\Omega$  series resistance in both the High and Low states of the output. The design reduces line noise in applications such as memory address drivers, clock drivers, and bus receivers/transceivers.

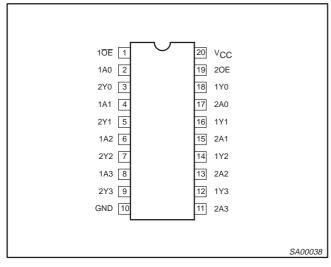
### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS T <sub>amb</sub> = 25°C; GND = 0V	TYPICAL	UNIT				
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay An to Yn	$C_L = 50 pF; V_{CC} = 5V$	2.9	ns				
C <sub>IN</sub>	Input capacitance	$V_{I} = 0V \text{ or } V_{CC}$	3	pF				
C <sub>OUT</sub>	Output capacitance	Outputs disabled; $V_0 = 0V$ or $V_{CC}$	7	pF				
I <sub>CCZ</sub>	Total supply current	Outputs disabled; V <sub>CC</sub> = 5.5V	50	μΑ				
ORDERING	ORDERING INFORMATION							

#### **ORDERING INFORMATION**

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
20-Pin Plastic DIP	-40°C to +85°C	74ABT2241 N	74ABT2241 N	SOT146-1
20-Pin plastic SO	-40°C to +85°C	74ABT2241 D	74ABT2241 D	SOT163-1
20-Pin Plastic SSOP Type II	-40°C to +85°C	74ABT2241 DB	74ABT2241 DB	SOT339-1
20-Pin Plastic TSSOP Type I	-40°C to +85°C	74ABT2241 PW	7ABT2241PW DH	SOT360-1

### **PIN CONFIGURATION**

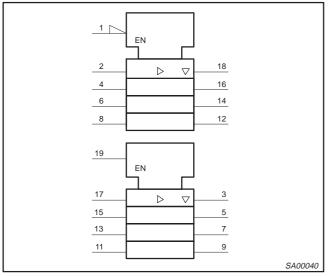


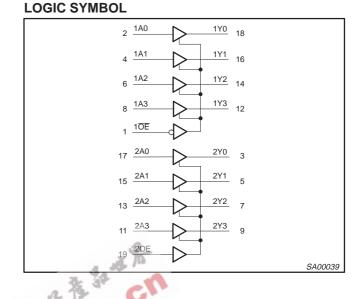
### **PIN DESCRIPTION**

PIN NUMBER	SYMBOL	NAME AND FUNCTION			
2, 4, 6, 8	1A0 – 1A3	Data inputs			
17, 15, 13, 11	2A0 – 2A3	Data inputs			
18, 16, 14, 12	1Y0 – 1Y3	Data outputs			
3, 5, 7, 9	2Y0 – 2Y3	Data outputs			
1, 19	1 <u>0E</u> , 20E	Output enables			
10	GND	Ground (0V)			
20	V <sub>CC</sub>	Positive supply voltage			

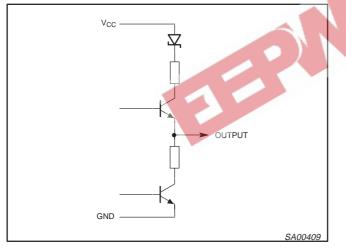
74ABT2241

### LOGIC SYMBOL (IEEE/IEC)





### SCHEMATIC OF EACH OUTPUT



### FUNCTION TABLE

C	INPU	OUTF	PUTS		
10E	1An	20E	2An	1Yn	2Yn
L	L	Н	L	L	L
L	н	н	н	н	н
н	х	L	х	Z	Z

Н = High voltage level

L = Low voltage level

= Don't care Х

Ζ = High impedance "off" state

### **ABSOLUTE MAXIMUM RATINGS<sup>1, 2</sup>**

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V <sub>CC</sub>	DC supply voltage		-0.5 to +7.0	V
I <sub>IK</sub>	DC input diode current	V <sub>1</sub> < 0	-18	mA
VI	DC input voltage <sup>3</sup>		-1.2 to +7.0	V
I <sub>OK</sub>	DC output diode current	V <sub>O</sub> < 0	-50	mA
V <sub>OUT</sub>	DC output voltage <sup>3</sup>	output in Off or High state	-0.5 to +5.5	V
I <sub>OUT</sub>	DC output current	output in Low state	128	mA
T <sub>stg</sub>	Storage temperature range		-65 to 150	°C

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction

temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 74ABT2241

### **RECOMMENDED OPERATING CONDITIONS**

SYMBOL	PARAMETER	LIM	UNIT	
		Min	Max	
V <sub>CC</sub>	DC supply voltage	4.5	5.5	V
VI	Input voltage	0	V <sub>CC</sub>	V
V <sub>IH</sub>	High-level input voltage	2.0		V
V <sub>IL</sub>	Low-level Input voltage		0.8	V
I <sub>ОН</sub>	High-level output current		-32	mA
I <sub>OL</sub>	Low-level output current		12	mA
Δt/Δv	Input transition rise or fall rate	0	5	ns/V
T <sub>amb</sub>	Operating free-air temperature range	-40	+85	°C

### DC ELECTRICAL CHARACTERISTICS

			-					
SYMBOL	PARAMETER	TEST CONDITIONS	Tai	T <sub>amb</sub> = +25°C			T <sub>amb</sub> = −40°C to +85°C	
		CO.	Min	Тур	Max	Min	Max	1
V <sub>IK</sub>	Input clamp voltage	$V_{CC} = 4.5V; I_{IK} = -18mA$		-0.9	-1.2		-1.2	V
		$V_{CC}$ = 4.5V; $I_{OH}$ = -3mA; $V_I$ = $V_{IL}$ or $V_{IH}$	2.5	2.9		2.5		V
V <sub>OH</sub>	High-level output voltage	$V_{CC} = 5.0V$ ; $I_{OH} = -3mA$ ; $V_I = V_{IL}$ or $V_{IH}$	3.0	3.4		3.0		V
		$V_{CC}$ = 4.5V; 1 <sub>OH</sub> = -32mA; V <sub>I</sub> = V <sub>IL</sub> or V <sub>IH</sub>	2.0	2.4		2.0		V
V <sub>OL</sub>	Low-level output voltage	$V_{CC}$ = 4.5V; $I_{OL}$ = 5mA; $V_I$ = $V_{IL}$ or $V_{IH}$		0.32	0.55		0.55	V
VOL	Low-level output voltage	$V_{CC}$ = 4.5V; I <sub>OL</sub> = 12mA; V <sub>I</sub> = V <sub>IL</sub> or V <sub>IH</sub>			0.8		0.8	V
lı	Input leakage current	$V_{CC}$ = 5.5V; $V_I$ = GND or 5.5V		±0.01	±1.0		±1.0	μA
I <sub>OFF</sub>	Power-off leakage current	$V_{CC}$ = 0.0V; V <sub>I</sub> or V <sub>O</sub> $\leq$ 4.5V		±5.0	±100		±100	μA
I <sub>PU</sub> /I <sub>PD</sub>	Power-up/down 3-State output current <sup>3</sup>	$\begin{array}{l} V_{\underline{CC}} = 2.0V; \ V_{O} = 0.5V; \ V_{I} = GND \ or \ V_{CC}; \\ V_{OE} = V_{CC}; \ V_{OE} = GND \end{array}$		±5.0	±50		±50	μA
I <sub>OZH</sub>	3-State output High current	$V_{CC}$ = 5.5V; $V_{O}$ = 2.7V; $V_{I}$ = $V_{IL}$ or $V_{IH}$		5.0	50		50	μA
I <sub>OZL</sub>	3-State output Low current	$V_{CC}$ = 5.5V; $V_{O}$ = 0.5V; $V_{I}$ = $V_{IL}$ or $V_{IH}$		-5.0	-50		-50	μA
I <sub>CEX</sub>	Output High leakage current	$V_{CC}$ = 5.5V; $V_{O}$ = 5.5V; $V_{I}$ = GND or $V_{CC}$		5.0	50		50	μA
Ι <sub>Ο</sub>	Output current <sup>1</sup>	$V_{CC} = 5.5V; V_{O} = 2.5V$	-50	-100	-180	-50	-180	mA
I <sub>CCH</sub>		$V_{CC}$ = 5.5V; Outputs High, $V_I$ = GND or $V_{CC}$		50	250		250	μA
I <sub>CCL</sub>	Quiescent supply current	$V_{CC}$ = 5.5V; Outputs Low, $V_{I}$ = GND or $V_{CC}$		24	30		30	mA
I <sub>CCZ</sub>		$V_{CC}$ = 5.5V; Outputs 3–State; V <sub>I</sub> = GND or V <sub>CC</sub>		50	250		250	μΑ
		Outputs enabled, one input at 3.4V, other inputs at V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5V		0.5	1.5		1.5	mA
$\Delta I_{CC}$	Additional supply current per input pin <sup>2</sup>	Outputs 3-State, one data input at 3.4V, other inputs at V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5V		50	250		250	μΑ
		Outputs 3-State, one enable input at 3.4V, other inputs at V <sub>CC</sub> or GND; $V_{CC} = 5.5V$		0.5	1.5		1.5	mA

NOTES:

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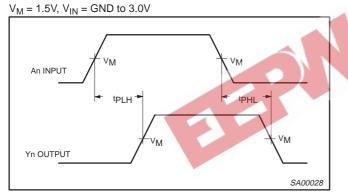
- 1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
- 2. This is the increase in supply current for each input at 3.4V.
- This parameter is valid for any V<sub>CC</sub> between 0V and 2.1V with a transition time of up to 10msec. For V<sub>CC</sub> = 2.1V to V<sub>CC</sub> = 5V  $\pm$  10%, a transition time of up to 100 µsec is permitted. 3.

### **AC CHARACTERISTICS**

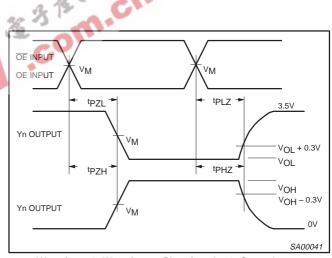
GND = 0V;  $t_R$  =  $t_F$  = 2.5ns;  $C_L$  = 50pF,  $R_L$  = 500 $\Omega$ 

					LIMI	ſS		
SYMBOL	PARAMETER	WAVEFORM	T <sub>2</sub> V	amb = +25° ′CC = +5.0′	C V	T <sub>amb</sub> = -40 V <sub>CC</sub> = +5	°C to +85°C .0V ±0.5V	UNIT
			Min	Тур	Max	Min	Max	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay An to Yn	1	1.0 1.0	2.7 3.9	4.3 5.3	1.0 1.0	4.7 5.6	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output enable time to High and Low level	2	1.1 2.1	3.3 5.4	4.8 7.6	1.1 2.1	5.8 8.4	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output disable time from High and Low level	2	1.7 1.7	<b>3.8</b> 3.4	5.6 5.8	1.7 1.7	6.6 6.4	ns
AC WAVE	FORMS	~ 3	なが	CI				

### **AC WAVEFORMS**



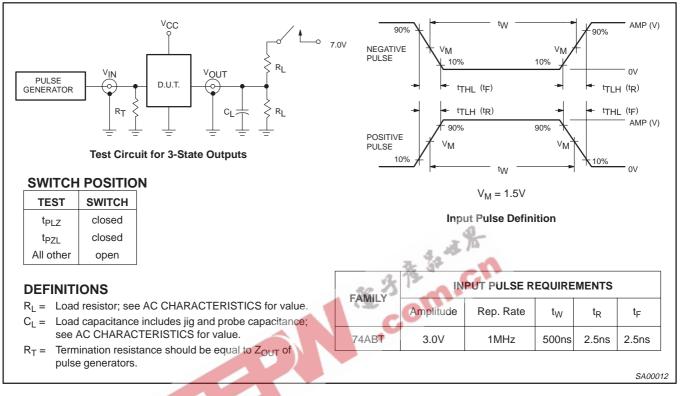
Waveform 1. Waveforms Showing the Input (An) to Output (Yn) Propagation Delays



Waveform 2. Waveforms Showing the 3-State Output **Enable and Disable Times** 

### 74ABT2241

### **TEST CIRCUIT AND WAVEFORMS**



# D $\mathsf{M}_\mathsf{E}$ seating plane 11. ⊢⊕ w( (e 11 $M_{H}$ pin 1 index 10 10 mm 5 0 scale DIMENSIONS (inch dimensions are derived from the original mm dimensions) Т (1) Т Т Т

UNIT	A max.	A <sub>1</sub> min.	A <sub>2</sub> max.	b	b <sub>1</sub>	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	e <sub>1</sub>	L	ME	M <sub>H</sub>	w	Z <sup>(1)</sup> max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	0.36 0.23	26.92 26.54	6.40 6.22	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.0
inches	0.17	0.020	0.13	0.068 0.051	0.021 0.015	0.014 0.009	1.060 1.045	0.25 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.078

#### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN				
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT146-1			SC603			<del>-92-11-17</del> 95-05-24	

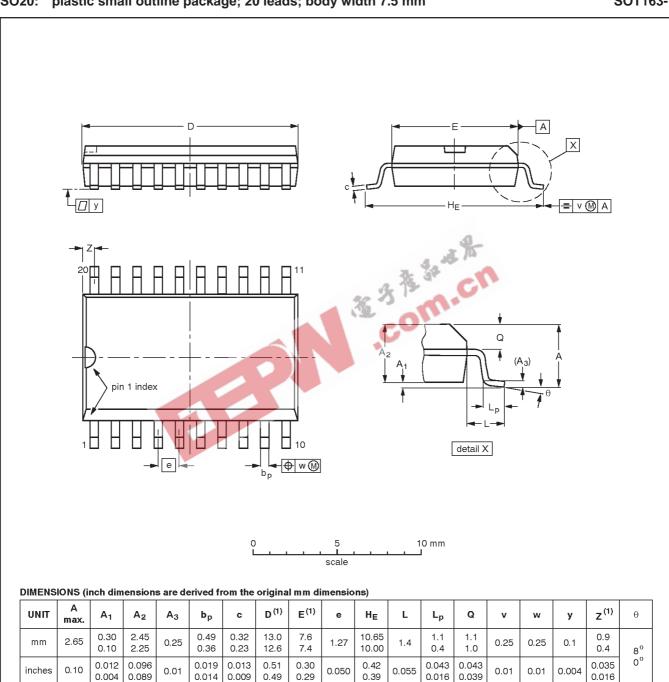
74ABT2241

DIP20: plastic dual in-line package; 20 leads (300 mil)

SOT146-1

74ABT2241

# Octal buffer with $30\Omega$ series termination resistors (3-State)



### SO20: plastic small outline package; 20 leads; body width 7.5 mm

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

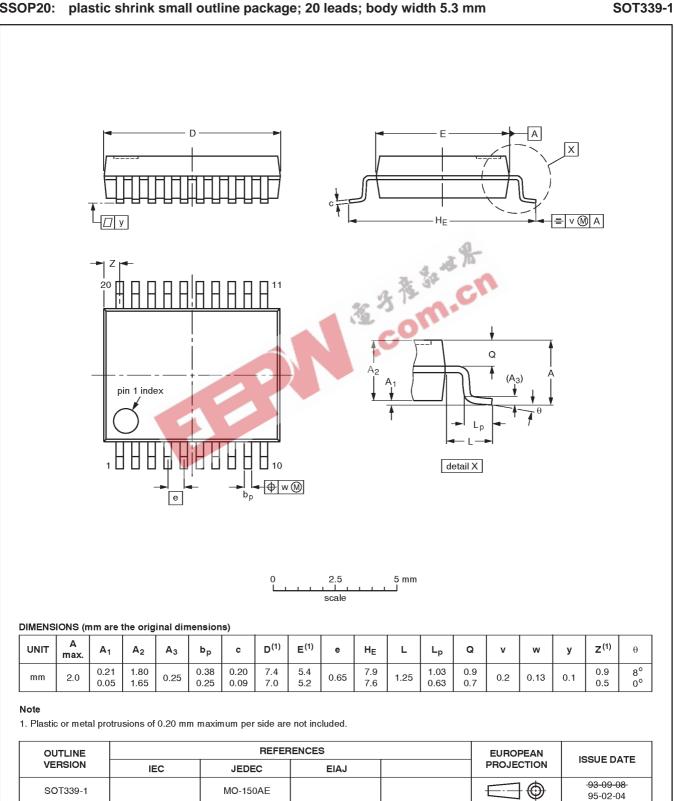
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC EIAJ			PROJECTION	ISSUE DATE	
SOT163-1	075E04	MS-013AC				<del>-92-11-17</del> 95-01-24	

SOT163-1

#### Product specification

### Octal buffer with $30\Omega$ series termination resistors (3-State)

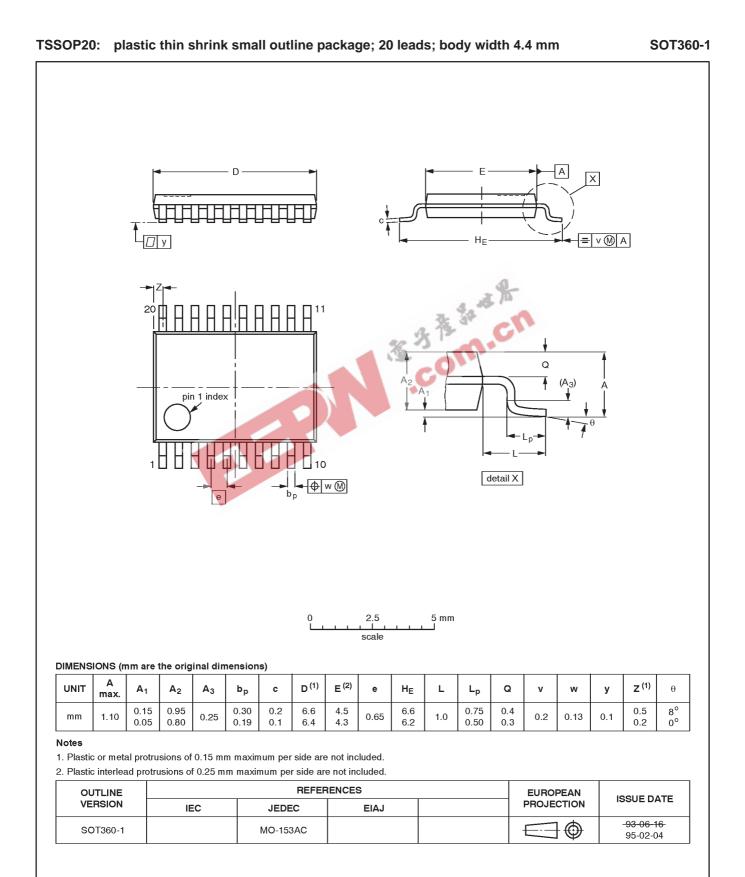
# 74ABT2241



### SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

1996 Sep 30

74ABT2241



74ABT2241

NOTES



74ABT2241



DEFINITIONS						
Data Sheet Identification	Product Status	Definition				
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.				
Preliminary Specification	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.				
Product Specification	Full Production	This data sheet contains Final Specifications. Philips Semiconductors reserves the right to make changes at any time without notice, in order to improve design and supply the best possible product.				

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